



PATENT APPLICATION

Sheet 1 of 3

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

10007286-1

APPLICATION NO.

09/975,297

CONFIRMATION NO.

APPLICANT

Ossipov et al.

FILING DATE

10/12/01

GROUP

2822

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
	1A				
	1B				
	1C				
	1D				
	1E				
	1F				
	1G				
	1H				
	1I				
	1J				
	1K				

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	TRANSLATION	
						YES	NO
	1L						
	1M						
	1N						
	1O						
	1P						

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

1Q	G.G.P. van GORKOM et al., "Performance of Silicon Cold Cathodes", September 30, 1985, J. Vac. Sci. Technol. B 4(1), Jan/Feb 1986, pp. 108-111.
1R	A.M.E. Hoeberechts et al., "Design, Technology, and Behavior of a Silicon Avalanche Cathode", October 8, 1985, J. Vac. Sci. Technol. B 4(1), Jan/Feb 1986, pp. 105-107.
1S	E.A. Hijzen et al., "Avalanche Cold Cathodes with 10% Emission Efficiency", September 8-10, 1988, ESSDERC'98 Proceedings of the 28th European Solid-State Device Research Conference, pp. 584-587.

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1Q	Yokoo et al., "Experiments of highly emissive metal-oxide-semiconductor electron tunneling cathode", May/June 1996, J. Vac. Sci. Technol. B 14(3), 1996 American Vacuum Society, pp. 2096-2099.
1R	Akinwande, A.I. et al., "GaN Solid State Electron Emitter", Technical Digest of IVMC'97, Kyongju, Korea 1997, pp. 602-607.
1S	Lee, W.S. et al., "A Study on the Diamond Cold Cathode in FED", Asia Display 98, pp. 681-684.

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

1Q	Komoda et al., "Mechanism of efficient and stable surface-emitting cold cathode based on porous polycrystalline silicon films", May/June 1999, J. Vac. Sci. Technol. B 17(3), 1999 American Vacuum Society, pp. 1076-1079.
1R	
1S	

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